



VNQ830PEP

QUAD CHANNEL HIGH SIDE DRIVER

TARGET SPECIFICATION

TYPE	$R_{DS(on)}$	I_{OUT}	V_{CC}
VNQ830PEP	60 m Ω (*)	14 A (*)	36 V

(*) Per each channel

- CMOS COMPATIBLE INPUTS
- OPEN DRAIN STATUS OUTPUTS
- ON STATE OPEN LOAD DETECTION
- OFF STATE OPEN LOAD DETECTION
- SHORTED LOAD PROTECTION
- UNDERVOLTAGE AND OVERVOLTAGE SHUTDOWN
- LOSS OF GROUND PROTECTION
- VERY LOW STAND-BY CURRENT
- REVERSE BATTERY PROTECTION (**)

DESCRIPTION

The VNQ830PEP is a monolithic device designed in STMicroelectronics VIPower M0-3 Technology, intended for driving any kind of load with one side connected to ground. Active V_{CC} pin voltage clamp protects the device

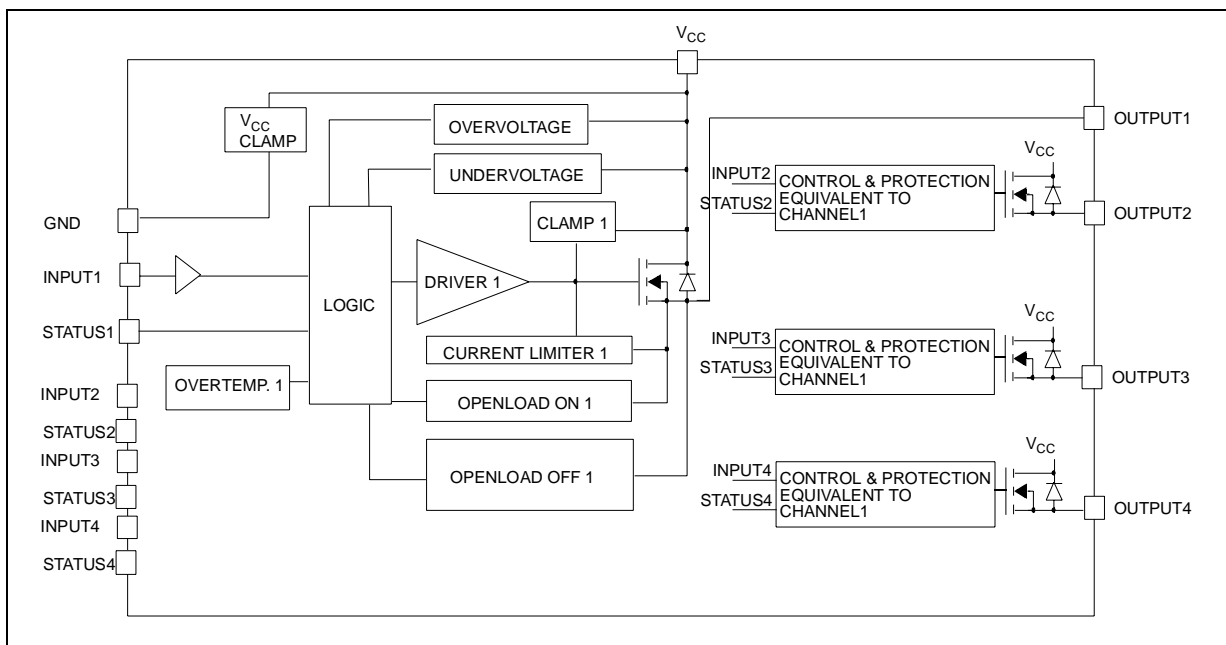


PowerSSO-24

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against low energy spikes (see ISO7637 transient compatibility table). Active current limitation combined with thermal shutdown and automatic restart protects the device against overload. The device detects open load condition both in on and off state. Output shorted to V_{CC} is detected in the off state. Device automatically turns off in case of ground pin disconnection.

BLOCK DIAGRAM



(**) See application schematic at page 8

Rev. 1

VNQ830PEP

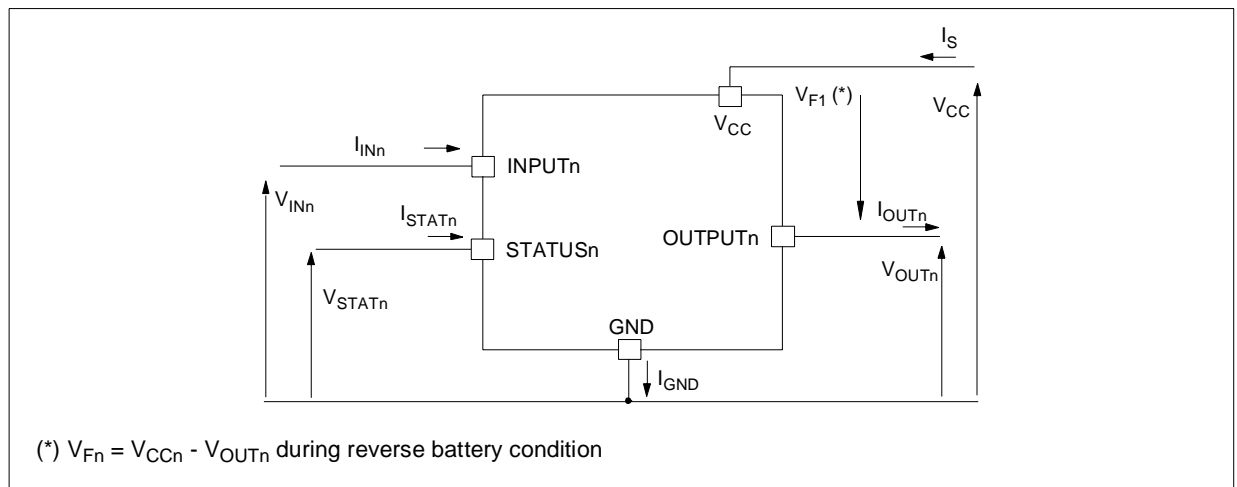
ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage	41	V
$-V_{CC}$	Reverse DC Supply Voltage	- 0.3	V
$-I_{GND}$	DC Reverse Ground Pin Current	- 200	mA
I_{OUT}	DC Output Current	Internally Limited	A
$-I_{OUT}$	Reverse DC Output Current	- 12	A
I_{IN}	DC Input Current	+/- 10	mA
I_{STAT}	DC Status Current	+/- 10	mA
V_{ESD}	Electrostatic Discharge (Human Body Model: R=1.5K Ω ; C=100pF)		
	- INPUT	4000	V
	- STATUS	4000	V
	- OUTPUT	5000	V
	- V_{CC}	5000	V
P_{tot}	Power Dissipation $T_C=25^\circ C$	83	W
T_j	Junction Operating Temperature	Internally Limited	$^\circ C$
T_C	Case Operating Temperature	- 40 to 150	$^\circ C$
T_{stg}	Storage Temperature	- 55 to 150	$^\circ C$

CONFIGURATION DIAGRAM (TOP VIEW) & SUGGESTED CONNECTIONS FOR UNUSED AND N.C. PINS

Connection / Pin	Status	N.C.	Output	Input
Floating	X	X	X	X
To Ground		X		Through 10K Ω resistor

CURRENT AND VOLTAGE CONVENTIONS



THERMAL DATA

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal Resistance Junction-case	1.5	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	52 (*)	°C/W

(*) When mounted on a standard single-sided FR-4 board with 0.5cm² of Cu (at least 35µm thick). Horizontal mounting and no artificial air flow.

ELECTRICAL CHARACTERISTICS (8V < V_{CC} < 36V; -40°C < T_j < 150°C, unless otherwise specified)

POWER OUTPUT

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{CC}	Operating Supply Voltage		5.5	13	36	V
V _{USD}	Undervoltage Shut-down		3	4	5.5	V
V _{OV}	Overvoltage Shut-down		36			V
R _{ON} (*)	On State Resistance	I _{OUT} = 2A; T _j = 25 °C I _{OUT} = 2A; V _{CC} > 8V			60 120	mΩ mΩ
I _S	Supply Current	Off State; V _{CC} = 13V; V _{IN} = V _{OUT} = 0V Off State; V _{CC} = 13V; V _{IN} = V _{OUT} = 0V; T _j = 25°C On State; V _{CC} = 13V; V _{IN} = 5V; I _{OUT} = 0A		20 20 8.5	60 40 13.5	µA µA mA
I _{L(off1)} (**)	Off State Output Current	V _{IN} = V _{OUT} = 0V	0		50	µA
I _{L(off2)} (**)	Off State Output Current	V _{IN} = 0V; V _{OUT} = 3.5V	-75		0	µA
I _{L(off3)} (**)	Off State Output Current	V _{IN} = V _{OUT} = 0V; V _{CC} = 13V; T _j = 125°C			5	µA
I _{L(off4)} (**)	Off State Output Current	V _{IN} = V _{OUT} = 0V; V _{CC} = 13V; T _j = 25°C			3	µA

(**) Per each channel

SWITCHING (V_{CC} = 13V)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
t _{d(on)}	Turn-on Delay Time	R _L = 6.5Ω from V _{IN} rising edge to V _{OUT} = 1.3V		30		µs
t _{d(off)}	Turn-off Delay Time	R _L = 6.5Ω from V _{IN} falling edge to V _{OUT} = 11.7V		30		µs
dV _{OUT} /dt _(on)	Turn-on Voltage Slope	R _L = 6.5Ω from V _{OUT} = 1.3V to V _{OUT} = 10.4V		See relative diagram		V/µs
dV _{OUT} /dt _(off)	Turn-off Voltage Slope	R _L = 6.5Ω from V _{OUT} = 11.7V to V _{OUT} = 1.3V		See relative diagram		V/µs

LOGIC INPUT

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{IL}	Input Low Level				1.25	V
I _{IL}	Low Level Input Current	V _{IN} = 1.25V	1			µA
V _{IH}	Input High Level		3.25			V
I _{IH}	High Level Input Current	V _{IN} = 3.25V			10	µA
V _{I(hyst)}	Input Hysteresis Voltage		0.5			V
V _{ICL}	Input Clamp Voltage	I _{IN} = 1mA I _{IN} = -1mA	6	6.8 -0.7	8	V V

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ELECTRICAL CHARACTERISTICS (continued)

V_{CC} - OUTPUT DIODE

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _F	Forward on Voltage	-I _{OUT} =1.3A; T _J =150°C			0.6	V

STATUS PIN

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{STAT}	Status Low Output Voltage	I _{STAT} = 1.6 mA			0.5	V
I _{LSTAT}	Status Leakage Current	Normal Operation; V _{STAT} = 5V			10	μA
C _{STAT}	Status Pin Input Capacitance	Normal Operation; V _{STAT} = 5V			100	pF
V _{SCL}	Status Clamp Voltage	I _{STAT} = 1mA I _{STAT} = - 1mA	6	6.8 -0.7	8	V

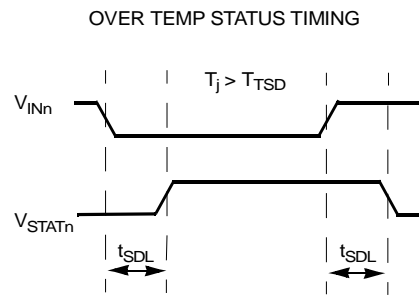
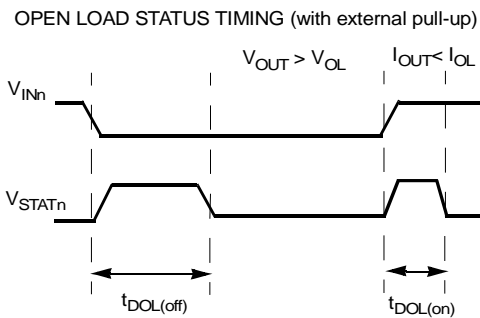
PROTECTIONS (Per each channel) (See note 1)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
T _{TSD}	Shut-down Temperature		150	175	200	°C
T _R	Reset Temperature		135			°C
T _{hyst}	Thermal Hysteresis		7	15		°C
t _{SDL}	Status Delay in Overload Conditions	T _J >T _{TSD}			20	μs
I _{lim}	Current limitation	V _{CC} =13V 5.5V < V _{CC} < 36V	14	18	23 23	A A
V _{demag}	Turn-off Output Clamp Voltage	I _{OUT} =2A; L= 6mH	V _{CC} -41	V _{CC} -48	V _{CC} -55	V

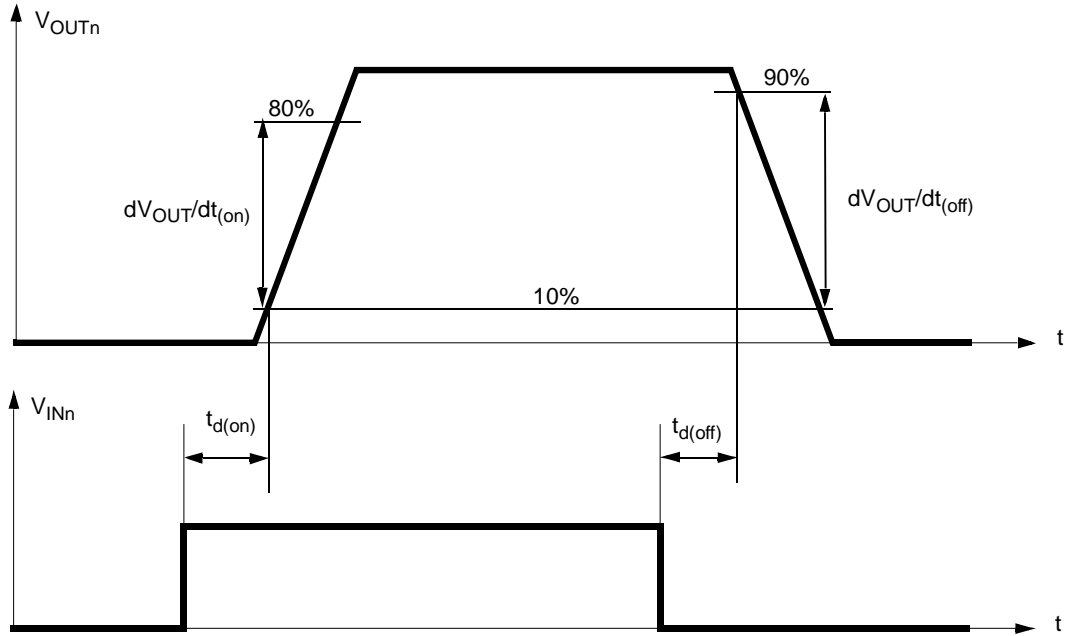
Note 1: To ensure long term reliability under heavy overload or short circuit conditions, protection and related diagnostic signals must be used together with a proper software strategy. If the device is subjected to abnormal conditions, this software must limit the duration and number of activation cycles.

OPENLOAD DETECTION

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
I _{OL}	Openload ON State Detection Threshold	V _{IN} =5V	35	70	140	mA
t _{DOL(on)}	Openload ON State Detection Delay	I _{OUT} =0A			200	μs
V _{OL}	Openload OFF State Voltage Detection Threshold	V _{IN} =0V	1.5	2.5	3.5	V
T _{DOL(off)}	Openload Detection Delay at Turn Off				1000	μs



Switching time Waveforms



TRUTH TABLE

CONDITIONS	INPUT	OUTPUT	STATUS
Normal Operation	L	L	H
	H	H	H
Current Limitation	L	L	H
	H	X	$(T_j < T_{TSD})$ H
	H	X	$(T_j > T_{TSD})$ L
Overtemperature	L	L	H
	H	L	L
Undervoltage	L	L	X
	H	L	X
Overvoltage	L	L	H
	H	L	H
Output Voltage $> V_{OL}$	L	H	L
	H	H	H
Output Current $< I_{OL}$	L	L	H
	H	H	L

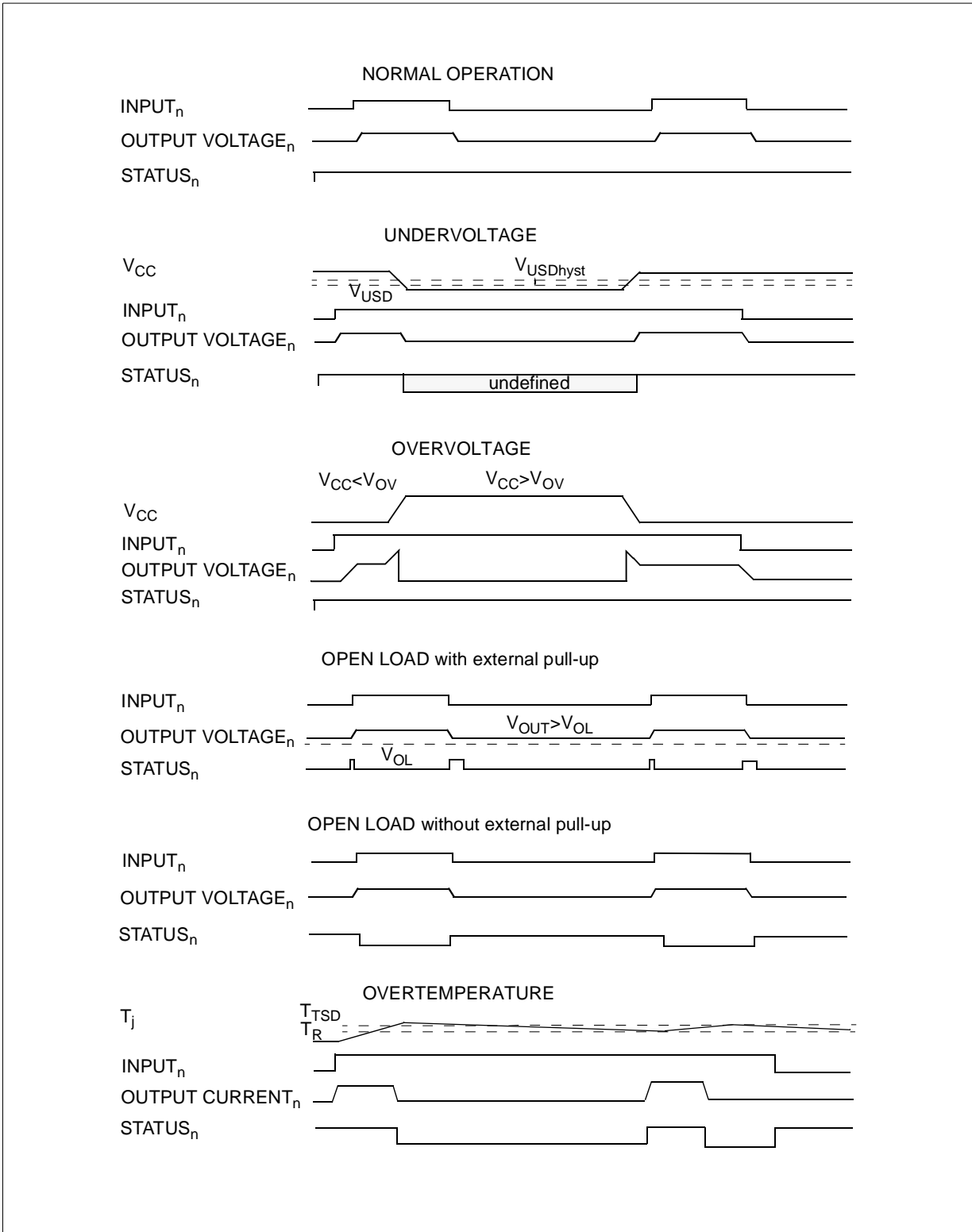
ELECTRICAL TRANSIENT REQUIREMENTS ON V_{CC} PIN

ISO T/R 7637/1 Test Pulse	TEST LEVELS				Delays and Impedance
	I	II	III	IV	
1	-25 V	-50 V	-75 V	-100 V	2 ms 10 Ω
2	+25 V	+50 V	+75 V	+100 V	0.2 ms 10 Ω
3a	-25 V	-50 V	-100 V	-150 V	0.1 μs 50 Ω
3b	+25 V	+50 V	+75 V	+100 V	0.1 μs 50 Ω
4	-4 V	-5 V	-6 V	-7 V	100 ms, 0.01 Ω
5	+26.5 V	+46.5 V	+66.5 V	+86.5 V	400 ms, 2 Ω

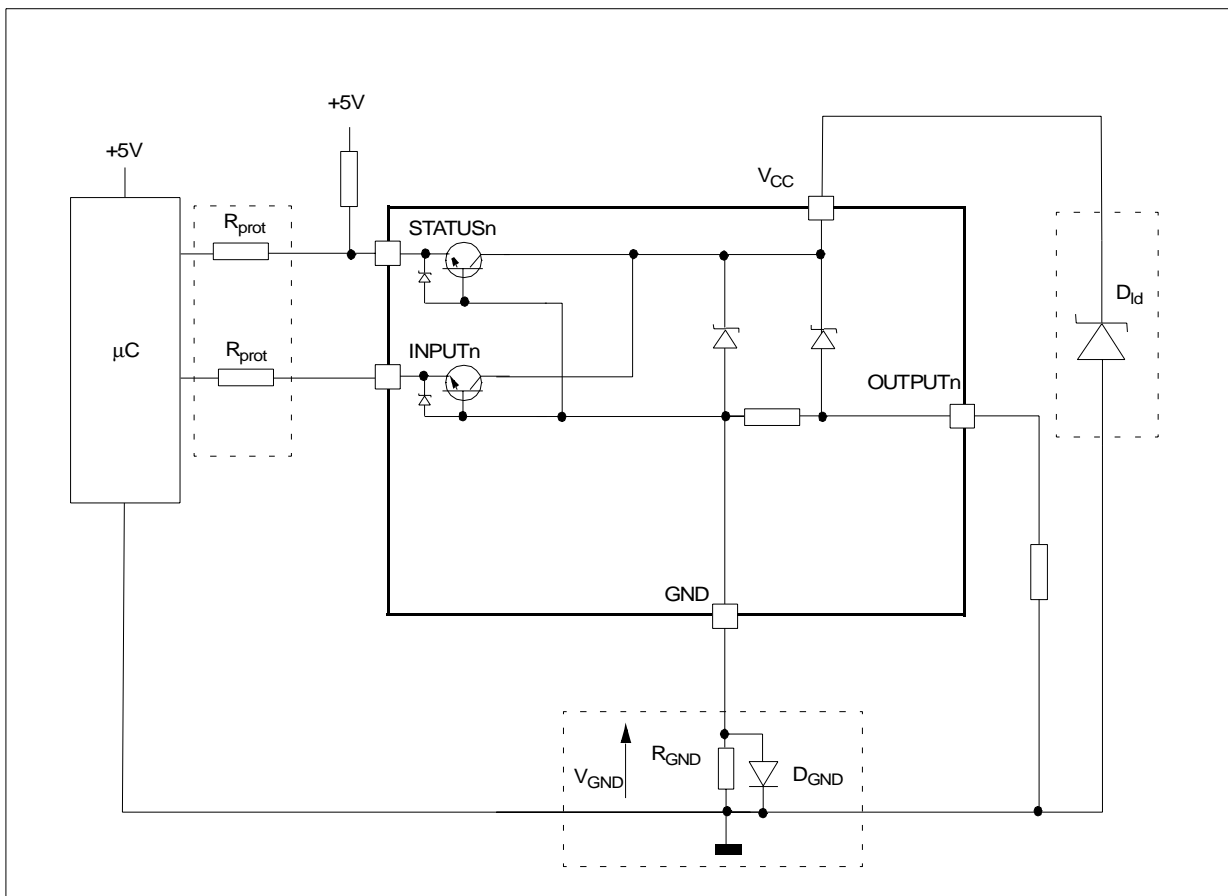
ISO T/R 7637/1 Test Pulse	TEST LEVELS RESULTS			
	I	II	III	IV
1	C	C	C	C
2	C	C	C	C
3a	C	C	C	C
3b	C	C	C	C
4	C	C	C	C
5	C	E	E	E

CLASS	CONTENTS
C	All functions of the device are performed as designed after exposure to disturbance.
E	One or more functions of the device is not performed as designed after exposure and cannot be returned to proper operation without replacing the device.

Figure 1: Waveforms



APPLICATION SCHEMATIC



GND PROTECTION NETWORK AGAINST REVERSE BATTERY

Solution 1: Resistor in the ground line (R_{GND} only). This can be used with any type of load.

The following is an indication on how to dimension the R_{GND} resistor.

- 1) $R_{GND} \leq 600mV / I_{S(on)max}$
- 2) $R_{GND} \geq (-V_{CC}) / (-I_{GND})$

where $-I_{GND}$ is the DC reverse ground pin current and can be found in the absolute maximum rating section of the device's datasheet.

Power Dissipation in R_{GND} (when $V_{CC} < 0$: during reverse battery situations) is:

$$P_D = (-V_{CC})^2 / R_{GND}$$

This resistor can be shared amongst several different HSD. Please note that the value of this resistor should be calculated with formula (1) where $I_{S(on)max}$ becomes the sum of the maximum on-state currents of the different devices.

Please note that if the microprocessor ground is not common with the device ground then the R_{GND} will produce a shift ($I_{S(on)max} * R_{GND}$) in the input thresholds and the status output values. This shift will vary

depending on how many devices are ON in the case of several high side drivers sharing the same R_{GND} .

If the calculated power dissipation leads to a large resistor or several devices have to share the same resistor then the ST suggests to utilize Solution 2 (see below).

Solution 2: A diode (D_{GND}) in the ground line.

A resistor ($R_{GND} = 1k\Omega$) should be inserted in parallel to D_{GND} if the device will be driving an inductive load.

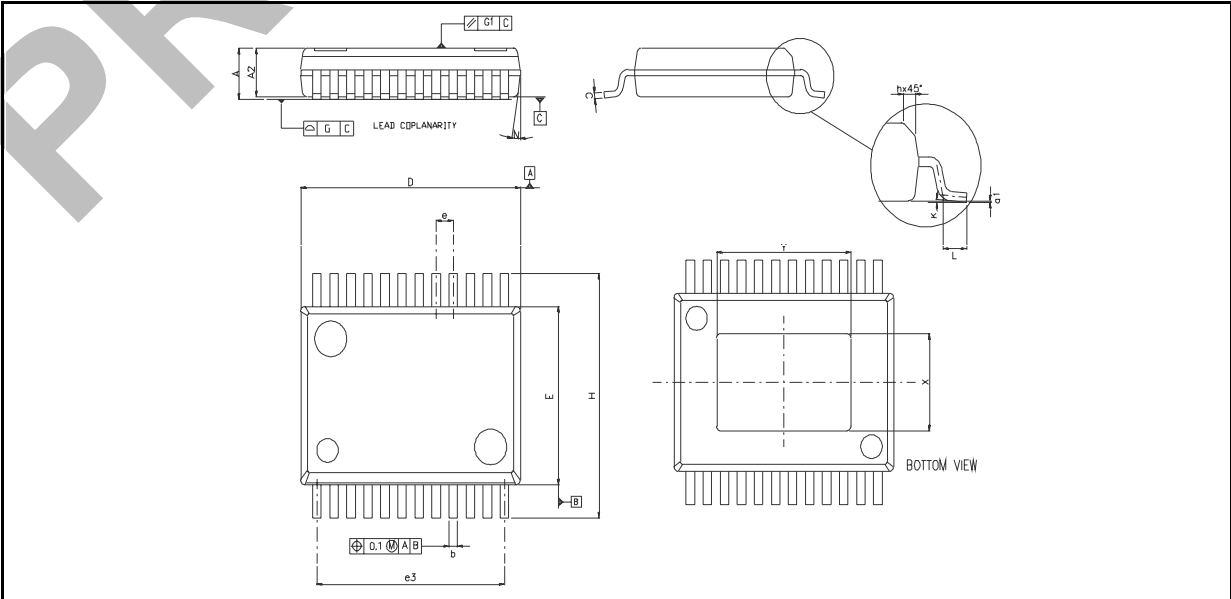
This small signal diode can be safely shared amongst several different HSD. Also in this case, the presence of the ground network will produce a shift ($\approx 600mV$) in the input threshold and the status output values if the microprocessor ground is not common with the device ground. This shift will not vary if more than one HSD shares the same diode/resistor network.

Series resistor in INPUT and STATUS lines are also required to prevent that, during battery voltage transient, the current exceeds the Absolute Maximum Rating.

Safest configuration for unused INPUT and STATUS pin is to leave them unconnected.

PowerSSO-24™ MECHANICAL DATA

DIM.	mm.		
	MIN.	TYP	MAX.
A	1.9		2.22
A2	1.9		2.15
a1	0		0.07
b	0.34	0.4	0.46
c	0.23		0.32
D	10.2		10.4
E	7.4		7.6
e		0.8	
e3		8.8	
G			0.1
G1			0.06
H	10.1		10.5
h			0.4
L	0.55		0.85
N			10°
X	3.9		4.3
Y	6.1		6.5



REVISION HISTORY

Date	Revision	Description of Changes
June 2004	1	<ul style="list-style-type: none">- Current and voltage convention update (page 2).- "Configuration diagram (top view) & suggested connections for unused and n.c. pins" insertion (page 2).- V_{CC} - OUTPUT DIODE section update (page 4).- PROTECTIONS note insertion (page 4).- Disclamers update (page 11).

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